

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a semiconductor device comprises: forming a first pattern in a first region over a semiconductor substrate; forming a second pattern in a second region separated from the first region over the semiconductor substrate; depositing an interlayer insulation film to cover the first and second patterns; forming a photoresist film on the interlayer insulation film; treating the photoresist film in stepper exposure and development to form a photoresist pattern of a photomask having its device pattern matched with the first pattern and its alignment marks matched with the second pattern; selectively etching off the interlayer insulation film over the first and second patterns, with the photoresist pattern; and after removing the photoresist pattern, flattening the interlayer insulation film to expose the surfaces of the first and second patterns, respectively.